



# STP22NM50 - STP22NM50FP STB22NM50 - STB22NM50-1

N-CHANNEL 500V - 0.16Ω - 20A TO-220/FP/D<sup>2</sup>PAK/I<sup>2</sup>PAK  
MDmesh™ Power MOSFET

## ADVANCED DATA

| TYPE        | V <sub>DSS</sub> | R <sub>DS(on)</sub> | R <sub>ds(on)</sub> *Q <sub>g</sub> | I <sub>D</sub> |
|-------------|------------------|---------------------|-------------------------------------|----------------|
| STP22NM50   | 500 V            | <0.215Ω             | 6.4 Ω*nC                            | 20 A           |
| STP22NM50FP | 500 V            | <0.215Ω             | 6.4 Ω*nC                            | 20 A           |
| STB22NM50   | 500 V            | <0.215Ω             | 6.4 Ω*nC                            | 20 A           |
| STB22NM50-1 | 500 V            | <0.215Ω             | 6.4 Ω*nC                            | 20 A           |

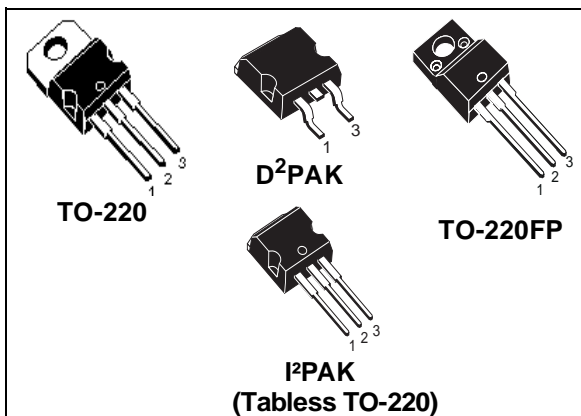
- TYPICAL R<sub>DS(on)</sub> = 0.16Ω
- HIGH dv/dt AND AVALANCHE CAPABILITIES
- 100% AVALANCHE TESTED
- LOW INPUT CAPACITANCE AND GATE CHARGE
- LOW GATE INPUT RESISTANCE

## DESCRIPTION

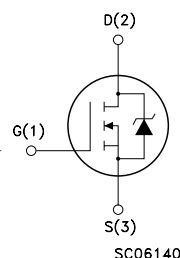
The MDmesh™ is a new revolutionary MOSFET technology that associates the Multiple Drain process with the Company's PowerMESH™ horizontal layout. The resulting product has an outstanding low on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the Company's proprietary strip technique yields overall dynamic performance that is significantly better than that of similar competition's products.

## APPLICATIONS

The MDmesh™ family is very suitable for increasing power density of high voltage converters allowing system miniaturization and higher efficiencies.



## INTERNAL SCHEMATIC DIAGRAM



## ABSOLUTE MAXIMUM RATINGS

| Symbol              | Parameter  | Value            |             | Unit |
|---------------------|--|------------------|-------------|------|
|                     |  | STP(B)22NM50(-1) | STP22NM50FP |      |
| V <sub>DS</sub>     | Drain-source Voltage (V <sub>GS</sub> = 0)           | 500              |             | V    |
| V <sub>DGR</sub>    | Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)         | 500              |             | V    |
| V <sub>GS</sub>     | Gate- source Voltage                                 | ±30              |             | V    |
| I <sub>D</sub>      | Drain Current (continuous) at T <sub>C</sub> = 25°C  | 20               | 20(*)       | A    |
| I <sub>D</sub>      | Drain Current (continuous) at T <sub>C</sub> = 100°C | 12.6             | 12.6(*)     | A    |
| I <sub>DM</sub> (●) | Drain Current (pulsed)                               | 80               | 80(*)       | A    |
| P <sub>TOT</sub>    | Total Dissipation at T <sub>C</sub> = 25°C           | 192              | 45          | W    |
|                     | Derating Factor                                      | 1.2              | 0.36        | W/°C |
| dv/dt(1)            | Peak Diode Recovery voltage slope                    | 15               |             | V/ns |
| V <sub>ISO</sub>    | Insulation Withstand Voltage (DC)                    | --               | 2000        | V    |
| T <sub>stg</sub>    | Storage Temperature                                  | -65 to 150       |             | °C   |
| T <sub>j</sub>      | Max. Operating Junction Temperature                  | 150              |             | °C   |

(●) Pulse width limited by safe operating area

(1) I<sub>SD</sub> ≤ 20A, di/dt ≤ 400A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>.

(\*) Limited only by maximum temperature allowed

**STP22NM50 / STP22NM50FP / STB22NM50 / STB22NM50-1****THERMAL DATA**

|                |  | TO-220/I <sup>2</sup> PAK/<br>D <sup>2</sup> PAK | TO-220FP |      |
|----------------|--|--|----------|------|
| Rthj-case      | Thermal Resistance Junction-case Max           | 0.65   | 2.8      | °C/W |
| Rthj-amb       | Thermal Resistance Junction-ambient Max        | 62.5   |          | °C/W |
| T <sub>I</sub> | Maximum Lead Temperature For Soldering Purpose | 300  |          | °C   |

**AVALANCHE CHARACTERISTICS**

| Symbol          | Parameter  | Max Value | Unit |
|-----------------|--|-----------|------|
| I <sub>AR</sub> | Avalanche Current, Repetitive or Not-Repetitive<br>(pulse width limited by T <sub>j</sub> max)                   | 10        | A    |
| E <sub>AS</sub> | Single Pulse Avalanche Energy<br>(starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = 5 A, V <sub>DD</sub> = 50 V) | 650       | mJ   |

**ELECTRICAL CHARACTERISTICS (T<sub>CASE</sub> = 25 °C UNLESS OTHERWISE SPECIFIED)**  
OFF

| Symbol               | Parameter   | Test Conditions   | Min. | Typ. | Max.    | Unit     |
|----------------------|---|---|------|------|---------|----------|
| V <sub>(BR)DSS</sub> | Drain-source Breakdown Voltage                        | I <sub>D</sub> = 250 µA, V <sub>GS</sub> = 0  | 500  |      |         | V        |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0) | V <sub>DS</sub> = Max Rating<br>V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C |      |      | 1<br>10 | µA<br>µA |
| I <sub>GSS</sub>     | Gate-body Leakage Current (V <sub>DS</sub> = 0)       | V <sub>GS</sub> = ±30V  |      |      | ±100    | nA       |

**ON (1)**

| Symbol              | Parameter                         | Test Conditions  | Min. | Typ. | Max.  | Unit |
|---------------------|-----------------------------------|--|------|------|-------|------|
| V <sub>GS(th)</sub> | Gate Threshold Voltage            | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA | 3    | 4    | 5     | V    |
| R <sub>DS(on)</sub> | Static Drain-source On Resistance | V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A                |      | 0.16 | 0.215 | Ω    |

**DYNAMIC**

| Symbol                   | Parameter                     | Test Conditions   | Min. | Typ. | Max. | Unit |
|--------------------------|-------------------------------|---|------|------|------|------|
| g <sub>fs</sub> (1)      | Forward Transconductance      | V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)</sub> max,<br>I <sub>D</sub> = 10A |      | 10   |      | S    |
| C <sub>iss</sub>         | Input Capacitance             | V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0                                   |      | 1480 |      | pF   |
| C <sub>oss</sub>         | Output Capacitance            |   |      | 285  |      | pF   |
| C <sub>rss</sub>         | Reverse Transfer Capacitance  |   |      | 34   |      | pF   |
| C <sub>oss eq.</sub> (2) | Equivalent Output Capacitance | V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 400V                                      |      | 130  |      | pF   |
| R <sub>g</sub>           | Gate Input Resistance         | f=1 MHz Gate DC Bias=0<br>Test Signal Level=20mV<br>Open Drain                          |      | 1.6  |      | Ω    |

1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.

2. C<sub>oss eq.</sub> is defined as a constant equivalent capacitance giving the same charging time as C<sub>oss</sub> when V<sub>DS</sub> increases from 0 to 80% V<sub>DSS</sub>.

**ELECTRICAL CHARACTERISTICS (CONTINUED)****SWITCHING ON**

| Symbol      | Parameter          | Test Conditions   | Min. | Typ. | Max. | Unit |
|-------------|--------------------|---|------|------|------|------|
| $t_{d(on)}$ | Turn-on Delay Time | $V_{DD} = 250\text{ V}$ , $I_D = 10\text{ A}$<br>$R_G = 4.7\Omega$ $V_{GS} = 10\text{ V}$<br>(see test circuit, Figure 3) |      | 24   |      | ns   |
| $t_r$       | Rise Time          |   |      | 16   |      | ns   |
| $Q_g$       | Total Gate Charge  | $V_{DD} = 400\text{ V}$ , $I_D = 20\text{ A}$ ,<br>$V_{GS} = 10\text{ V}$   |      | 40   | 56   | nC   |
| $Q_{gs}$    | Gate-Source Charge |   |      | 13   |      | nC   |
| $Q_{gd}$    | Gate-Drain Charge  |   |      | 19   |      | nC   |

**SWITCHING OFF**

| Symbol        | Parameter             | Test Conditions   | Min. | Typ. | Max. | Unit |
|---------------|-----------------------|---|------|------|------|------|
| $t_{r(Voff)}$ | Off-voltage Rise Time | $V_{DD} = 400\text{ V}$ , $I_D = 20\text{ A}$ ,<br>$R_G = 4.7\Omega$ , $V_{GS} = 10\text{ V}$<br>(see test circuit, Figure 5) |      | 9    |      | ns   |
| $t_f$         | Fall Time             |   |      | 8.5  |      | ns   |
| $t_c$         | Cross-over Time       |   |      | 23   |      | ns   |

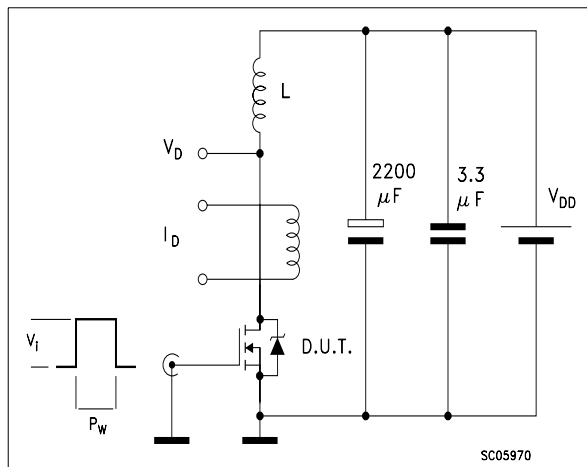
**SOURCE DRAIN DIODE**

| Symbol       | Parameter                     | Test Conditions  | Min. | Typ. | Max. | Unit          |
|--------------|-------------------------------|--|------|------|------|---------------|
| $I_{SD}$     | Source-drain Current          |  |      |      | 20   | A             |
| $I_{SDM(2)}$ | Source-drain Current (pulsed) |  |      |      | 80   | A             |
| $V_{SD(1)}$  | Forward On Voltage            | $I_{SD} = 20\text{ A}$ , $V_{GS} = 0$  |      |      | 1.5  | V             |
| $t_{rr}$     | Reverse Recovery Time         | $I_{SD} = 20\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ ,<br>$V_{DD} = 100\text{ V}$ , $T_j = 25^\circ\text{C}$<br>(see test circuit, Figure 5)  |      | 350  |      | ns            |
| $Q_{rr}$     | Reverse Recovery Charge       |  |      | 4.6  |      | $\mu\text{C}$ |
| $I_{RRM}$    | Reverse Recovery Current      |  |      | 26   |      | A             |
| $t_{rr}$     | Reverse Recovery Time         | $I_{SD} = 20\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ ,<br>$V_{DD} = 100\text{ V}$ , $T_j = 150^\circ\text{C}$<br>(see test circuit, Figure 5) |      | 435  |      | ns            |
| $Q_{rr}$     | Reverse Recovery Charge       |  |      | 5.9  |      | $\mu\text{C}$ |
| $I_{RRM}$    | Reverse Recovery Current      |  |      | 27   |      | A             |

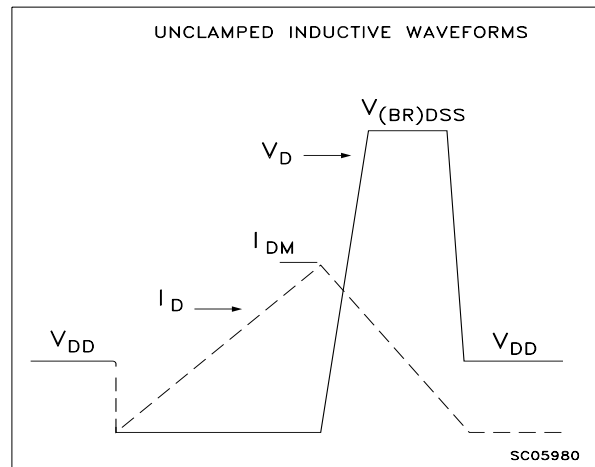
Note: 1. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.

2. Pulse width limited by safe operating area.

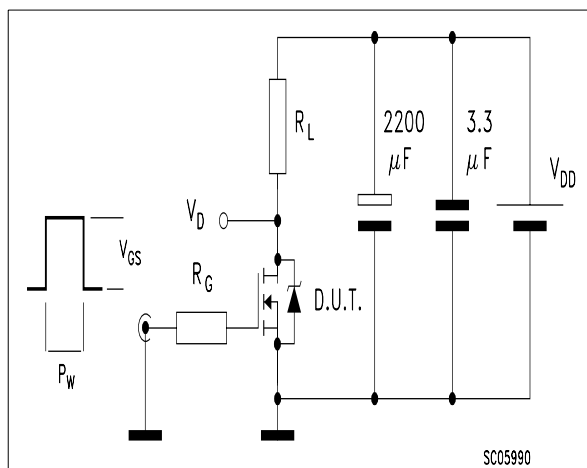
**Fig. 1: Unclamped Inductive Load Test Circuit**



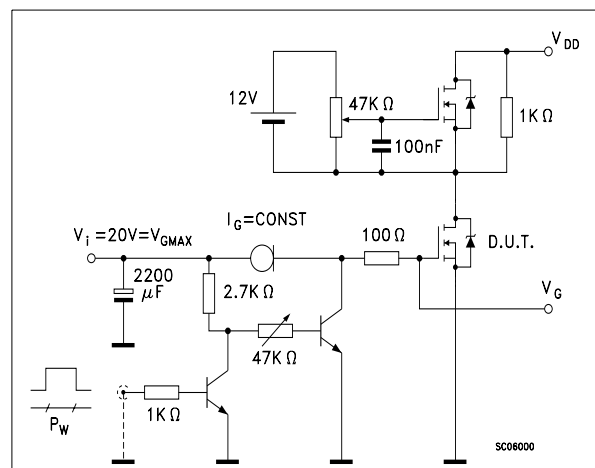
**Fig. 2: Unclamped Inductive Waveform**



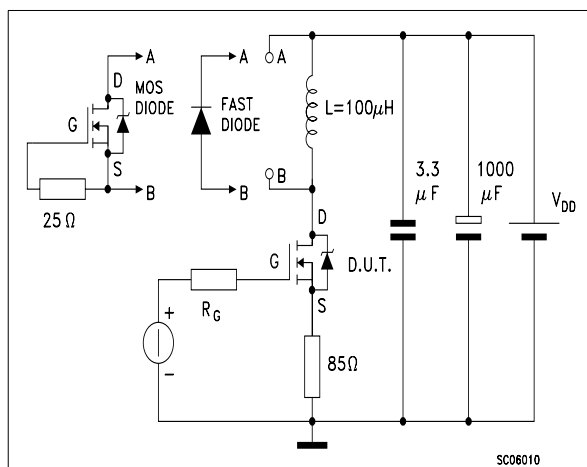
**Fig. 3: Switching Times Test Circuits For Resistive Load**



**Fig. 4: Gate Charge test Circuit**

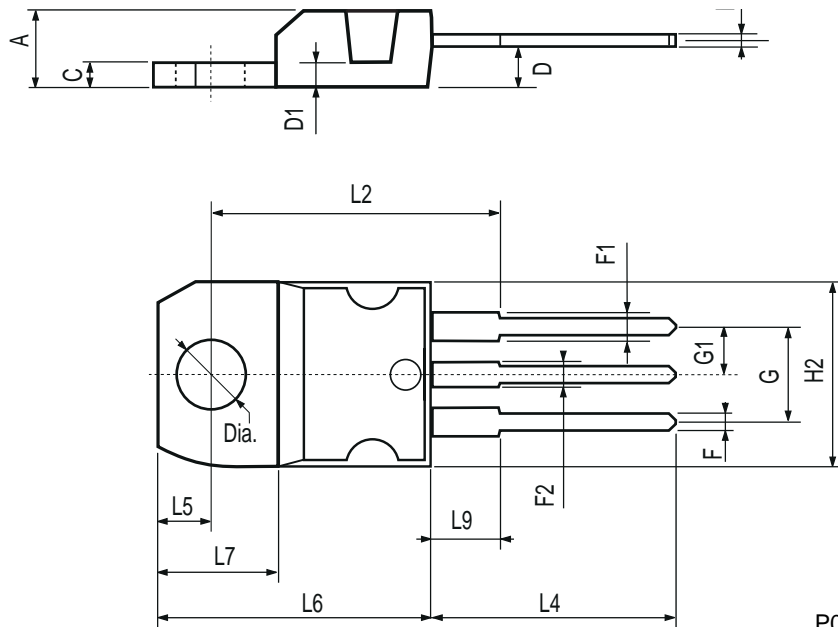


**Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times**



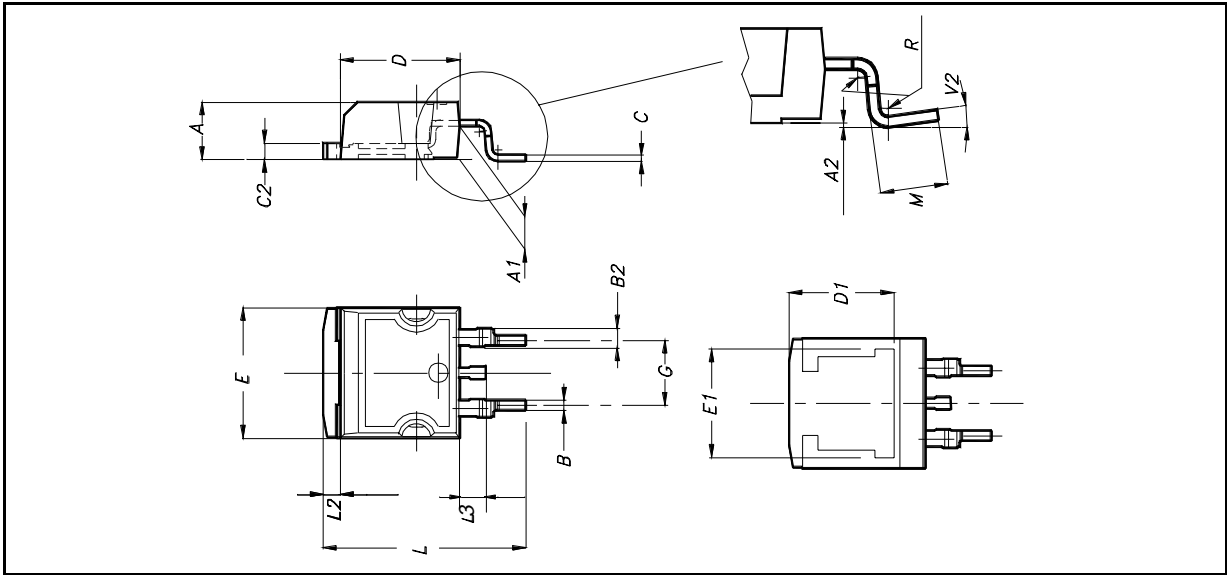
TO-220 MECHANICAL DATA

| DIM. | mm    |      |       | inch  |       |       |
|------|-------|------|-------|-------|-------|-------|
|      | MIN.  | TYP. | MAX.  | MIN.  | TYP.  | MAX.  |
| A    | 4.40  |      | 4.60  | 0.173 |       | 0.181 |
| C    | 1.23  |      | 1.32  | 0.048 |       | 0.051 |
| D    | 2.40  |      | 2.72  | 0.094 |       | 0.107 |
| D1   |       | 1.27 |       |       | 0.050 |       |
| E    | 0.49  |      | 0.70  | 0.019 |       | 0.027 |
| F    | 0.61  |      | 0.88  | 0.024 |       | 0.034 |
| F1   | 1.14  |      | 1.70  | 0.044 |       | 0.067 |
| F2   | 1.14  |      | 1.70  | 0.044 |       | 0.067 |
| G    | 4.95  |      | 5.15  | 0.194 |       | 0.203 |
| G1   | 2.4   |      | 2.7   | 0.094 |       | 0.106 |
| H2   | 10.0  |      | 10.40 | 0.393 |       | 0.409 |
| L2   |       | 16.4 |       |       | 0.645 |       |
| L4   | 13.0  |      | 14.0  | 0.511 |       | 0.551 |
| L5   | 2.65  |      | 2.95  | 0.104 |       | 0.116 |
| L6   | 15.25 |      | 15.75 | 0.600 |       | 0.620 |
| L7   | 6.2   |      | 6.6   | 0.244 |       | 0.260 |
| L9   | 3.5   |      | 3.93  | 0.137 |       | 0.154 |
| DIA. | 3.75  |      | 3.85  | 0.147 |       | 0.151 |



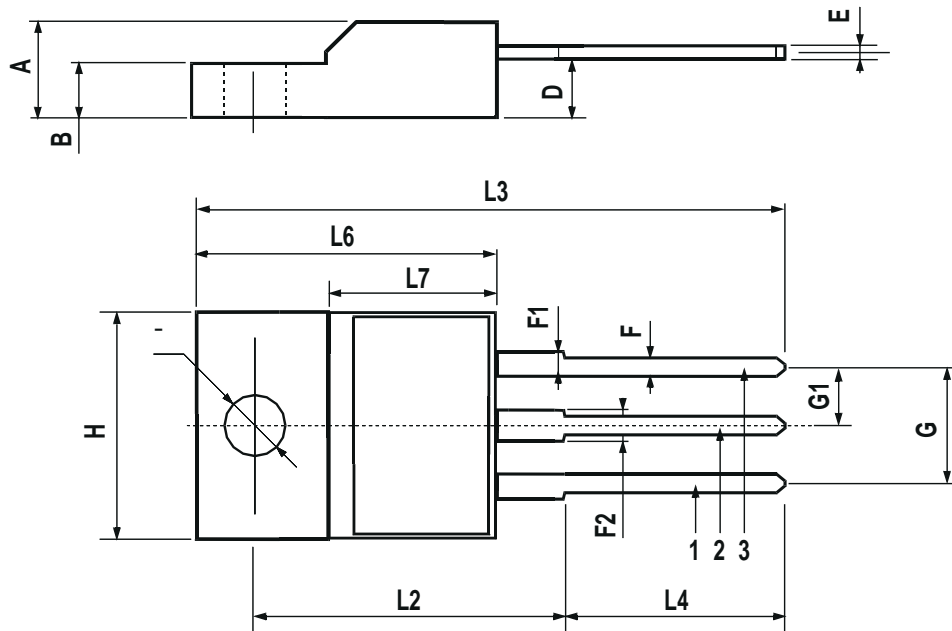
D<sup>2</sup>PAK MECHANICAL DATA

| DIM. | mm.  |     |       | inch  |       |       |
|------|------|-----|-------|-------|-------|-------|
|      | MIN. | TYP | MAX.  | MIN.  | TYP.  | MAX.  |
| A    | 4.4  |     | 4.6   | 0.173 |       | 0.181 |
| A1   | 2.49 |     | 2.69  | 0.098 |       | 0.106 |
| A2   | 0.03 |     | 0.23  | 0.001 |       | 0.009 |
| B    | 0.7  |     | 0.93  | 0.027 |       | 0.036 |
| B2   | 1.14 |     | 1.7   | 0.044 |       | 0.067 |
| C    | 0.45 |     | 0.6   | 0.017 |       | 0.023 |
| C2   | 1.23 |     | 1.36  | 0.048 |       | 0.053 |
| D    | 8.95 |     | 9.35  | 0.352 |       | 0.368 |
| D1   |      | 8   |       |       | 0.315 |       |
| E    | 10   |     | 10.4  | 0.393 |       |       |
| E1   |      | 8.5 |       |       | 0.334 |       |
| G    | 4.88 |     | 5.28  | 0.192 |       | 0.208 |
| L    | 15   |     | 15.85 | 0.590 |       | 0.625 |
| L2   | 1.27 |     | 1.4   | 0.050 |       | 0.055 |
| L3   | 1.4  |     | 1.75  | 0.055 |       | 0.068 |
| M    | 2.4  |     | 3.2   | 0.094 |       | 0.126 |
| R    |      | 0.4 |       |       | 0.015 |       |
| V2   | 0°   |     | 8°    |       |       |       |



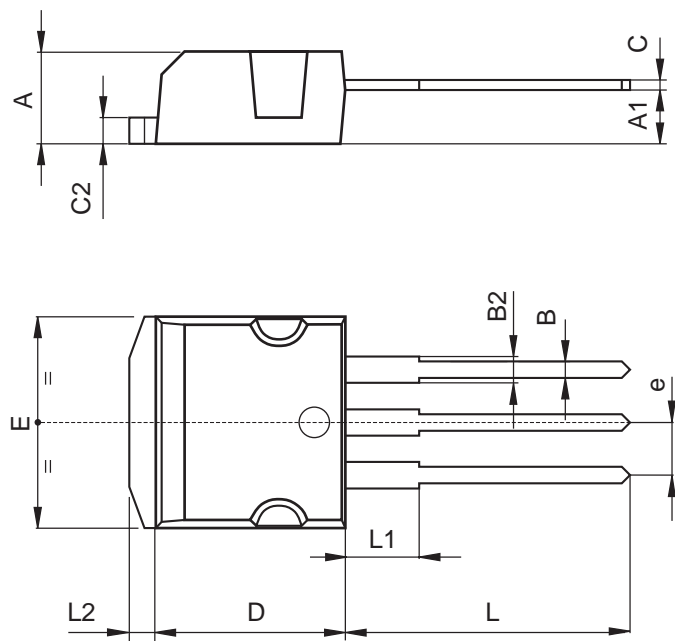
TO-220FP MECHANICAL DATA

| DIM. | mm   |      |      | inch  |       |       |
|------|------|------|------|-------|-------|-------|
|      | MIN. | TYP. | MAX. | MIN.  | TYP.  | MAX.  |
| A    | 4.4  |      | 4.6  | 0.173 |       | 0.181 |
| B    | 2.5  |      | 2.7  | 0.098 |       | 0.106 |
| D    | 2.5  |      | 2.75 | 0.098 |       | 0.108 |
| E    | 0.45 |      | 0.7  | 0.017 |       | 0.027 |
| F    | 0.75 |      | 1    | 0.030 |       | 0.039 |
| F1   | 1.15 |      | 1.7  | 0.045 |       | 0.067 |
| F2   | 1.15 |      | 1.7  | 0.045 |       | 0.067 |
| G    | 4.95 |      | 5.2  | 0.195 |       | 0.204 |
| G1   | 2.4  |      | 2.7  | 0.094 |       | 0.106 |
| H    | 10   |      | 10.4 | 0.393 |       | 0.409 |
| L2   |      | 16   |      |       | 0.630 |       |
| L3   | 28.6 |      | 30.6 | 1.126 |       | 1.204 |
| L4   | 9.8  |      | 10.6 | 0.385 |       | 0.417 |
| L6   | 15.9 |      | 16.4 | 0.626 |       | 0.645 |
| L7   | 9    |      | 9.3  | 0.354 |       | 0.366 |
| Ø    | 3    |      | 3.2  | 0.118 |       | 0.126 |



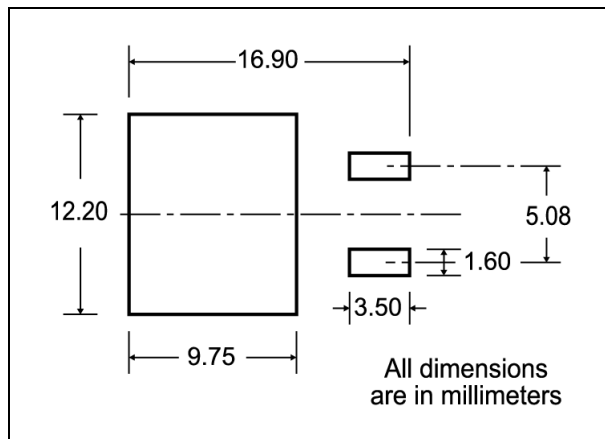
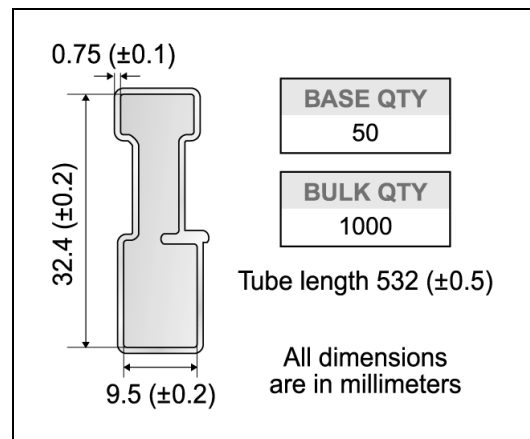
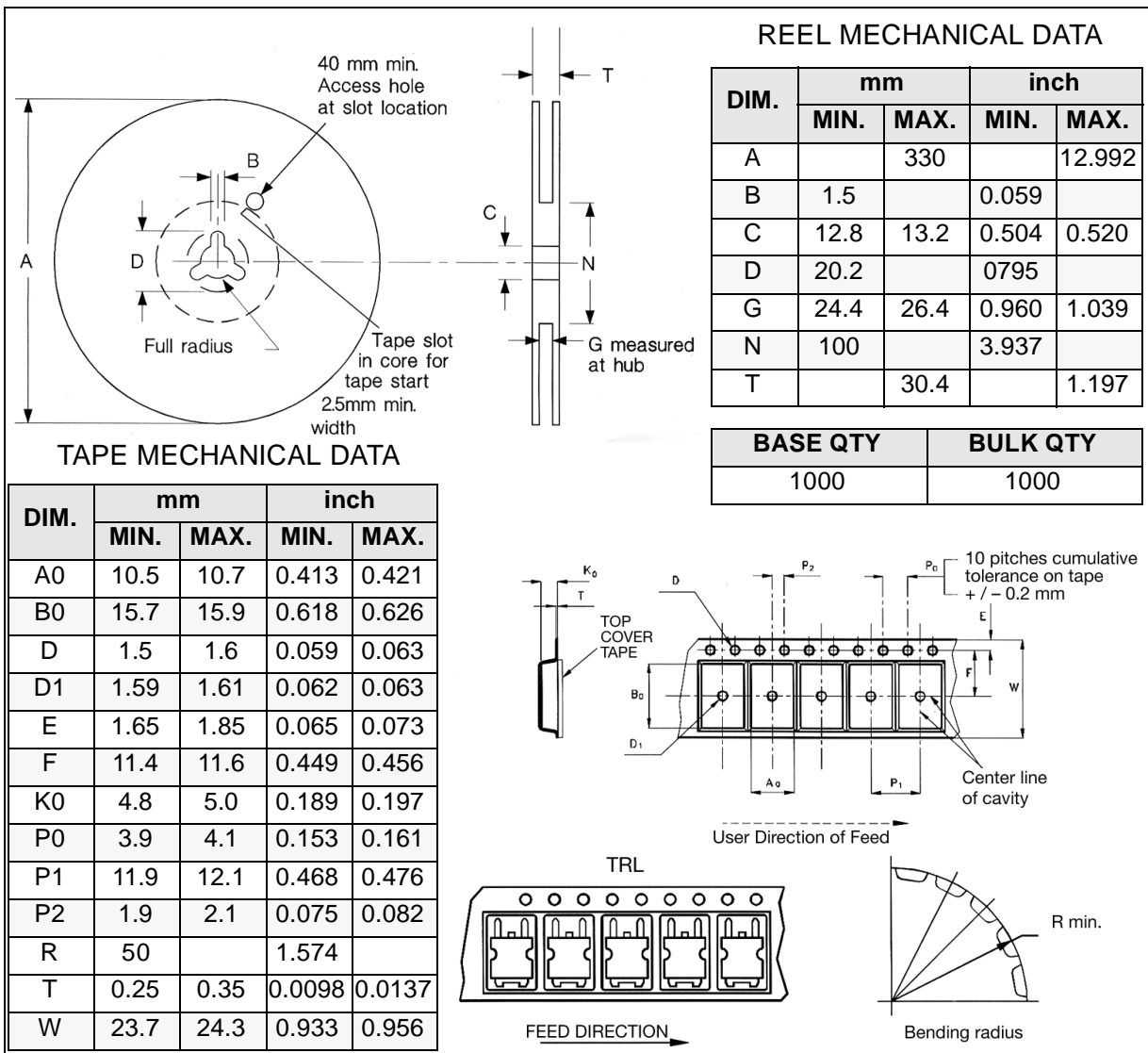
TO-262 (I<sup>2</sup>PAK) MECHANICAL DATA

| DIM. | mm   |      |      | inch  |      |       |
|------|------|------|------|-------|------|-------|
|      | MIN. | TYP. | MAX. | MIN.  | TYP. | MAX.  |
| A    | 4.4  |      | 4.6  | 0.173 |      | 0.181 |
| A1   | 2.49 |      | 2.69 | 0.098 |      | 0.106 |
| B    | 0.7  |      | 0.93 | 0.027 |      | 0.036 |
| B2   | 1.14 |      | 1.7  | 0.044 |      | 0.067 |
| C    | 0.45 |      | 0.6  | 0.017 |      | 0.023 |
| C2   | 1.23 |      | 1.36 | 0.048 |      | 0.053 |
| D    | 8.95 |      | 9.35 | 0.352 |      | 0.368 |
| e    | 2.4  |      | 2.7  | 0.094 |      | 0.106 |
| E    | 10   |      | 10.4 | 0.393 |      | 0.409 |
| L    | 13.1 |      | 13.6 | 0.515 |      | 0.531 |
| L1   | 3.48 |      | 3.78 | 0.137 |      | 0.149 |
| L2   | 1.27 |      | 1.4  | 0.050 |      | 0.055 |



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**D<sup>2</sup>PAK FOOTPRINT****TUBE SHIPMENT (no suffix)\*****TAPE AND REEL SHIPMENT (suffix "T4")\***

\* on sales type



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